

Data Sheet January 16, 2006 FN3751.3

Ultra Low Noise, Precision Operational Amplifier

The HA-5127/883 monolithic operational amplifier features an excellent combination of precision DC and wideband high speed characteristics. Utilizing the Intersil D.I. technology and advanced processing techniques, this unique design unites low noise precision instrumentation performance with high speed, wideband capability.

This amplifier's impressive list of features include low V_{OS} , wide gain-bandwidth, high open loop gain, and high CMRR. Additionally, this flexible device operates over a wide supply range while consuming only 120mW of power.

Using the HA-5127/883 allows designers to minimize errors while maximizing speed and bandwidth.

This device is ideally suited for low level transducer signal amplifier circuits. Other applications which can utilize the HA-5127/883's qualities include instrumentation amplifiers, pulse or RF amplifiers, audio preamplifiers, and signal conditioning circuits.

Ordering Information

PART NUMBER	WWW PART MARKING	T :M? RANGE (°C)	PACKAGE	PKG. DWG.#
HA2-5127/883	HA2-5127/883	-55 to +125	8 Pin Can	T8.C

Features

- This Circuit is Processed in Accordance to MIL-STD-883 and is Fully Conformant Under the Provisions of Paragraph 1.2.1.
- High Slew Rate7V/µs (Min)
- Low Noise Voltage (at 1kHz) 4.5nV/√Hz (Max)
- Low Offset Drift With Temperature 1.8μV/°C (Max)
- High Voltage Gain 700kV/V (Min)

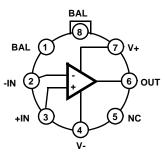
Applications

- · High Speed Signal Conditioners
- · Wide Bandwidth Instrumentation Amplifiers
- · Low Level Transducer Amplifiers
- · Fast, Low Level Voltage Comparators
- Highest Quality Audio Preamplifiers

Mulse/R Angliffers

Pinout

HA-5127/883 (METAL CAN) TOP VIEW



Absolute Maximum Ratings

Voltage Between V+ and V- Terminals .44V Differential Input Voltage (Note 2) .0.7V Voltage at Either Input Terminal .V+ to V Input Current .25mA Differential Output Current Full Short Circuit Protection Junction Temperature (T_J) .+175°C Storage Temperature Range -65°C to +150°C ESD Rating .2000V Lead Temperature (Soldering 10s) .+300°C

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Thermal Information

Thermal Resistance	$\theta_{\sf JA}$	θ_{JC}
Metal Can Package	155°C/W	67°C/W
Package Power Dissipation Limit at +75°C fo	or T _J ≤ +175 ^o	C
Metal Can Package		645mW
Package Power Dissipation Derating Factor	Above +75°C	
Metal Can Package		6.5mW/°C

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

Recommended Operating Conditions

TABLE 1. DC ELECTRICAL PERFORMANCE CHARACTERISTICS

Device Tested at: $V_{SUPPLY} = \pm 15V$, $R_{SOURCE} = 50\Omega$, $R_{LOAD} = 100k\Omega$, $V_{OUT} = 0V$, Unless Otherwise Specified.

			GROUP A		LIMITS		
PARAMETERS	SYMBOL	CONDITIONS	SUBGROUPS	TEMPERATURE	MIN	MAX	UNITS
Input Offset Voltage	V_{IO}	V _{CM} = 0V	1	+25°C	-100	100	μV
			2, 3	+125°C, -55°C	-300	300	μV
Input Bias Current	I _B	V _{CM} = 0V,	1	+25°C	-	80	nA
		$R_{S} = 10k\Omega, 50\Omega$ $\left(\frac{ + B + - B }{ - B }\right)$	2, 3	+125°C, -55°C	-	150	nA
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Input Offset Current	l _{iO}	$V_{CM} = 0V$,		+25°C	-70	75	nA
		$+R_S = 10kΩ$, $-R_S = 10kΩ$	2, 3	+125°C, -55°C	-135	135	nA
Common Mode Range	+CMR	V+ = +4.7V, V- = -25.3V	1	+25°C	10.3	-	V
			2, 3	+125°C, -55°C	10.3	-	V
	-CMR	V+ = +25.3V, V- = -4.7V	1	+25°C	-	-10.3	V
			2, 3	+125°C, -55°C	-	-10.3	V
Large Signal Voltage	+A _{VOL}	V_{OUT} = 0V and +10V, R_L = $2k\Omega$	4	+25°C	700	-	kV/V
Gain			5, 6	+125°C, -55°C	300	-	kV/V
	-A _{VOL}	V_{OUT} = 0V and -10V, R_L = $2k\Omega$	4	+25°C	700	-	kV/V
			5, 6	+125°C, -55°C	300	-	kV/V
Common Mode	+CMRR	ΔV _{CM} = +11V	1	+25°C	100	-	dB
Rejection Ratio		ΔV _{CM} = +10V	2, 3	+125°C, -55°C	100	-	dB
	-CMRR	ΔV _{CM} = -11V	1	+25°C	100	-	dB
		ΔV _{CM} = -10V	2, 3	+125°C, -55°C	100	-	dB
Output Voltage Swing	+V _{OUT1}	$R_L = 2k\Omega$	4	+25°C	11.5	-	V
			5, 6	+125°C, -55°C	11.5	-	V
	-V _{OUT1}	$R_L = 2k\Omega$	4	+25°C	-	-11.5	V
			5, 6	+125°C, -55°C	-	-11.5	V
	+V _{OUT2}	$R_L = 600\Omega$	4	+25°C	10	-	V
	$-V_{OUT2}$ R _L = 600Ω		4	+25°C	-	-10	V

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TABLE 1. DC ELECTRICAL PERFORMANCE CHARACTERISTICS (Continued)

Device Tested at: $V_{SUPPLY} = \pm 15V$, $R_{SOURCE} = 50\Omega$, $R_{LOAD} = 100k\Omega$, $V_{OUT} = 0V$, Unless Otherwise Specified.

			GROUP A		LIMITS		
PARAMETERS	SYMBOL	CONDITIONS	SUBGROUPS	TEMPERATURE	MIN	MAX	UNITS
Output Current	+l _{OUT}	V _{OUT} = -10V	4	+25°C	16.5	-	mA
	-I _{OUT}	V _{OUT} = +10V	4	+25°C	-	-16.5	mA
Quiescent Power	+I _{CC}	V _{OUT} = 0V, I _{OUT} = 0mA	1	+25°C	-	4	mA
Supply Current			2, 3	+125°C, -55°C	-	4	mA
	-I _{CC}	V _{OUT} = 0V, I _{OUT} = 0mA	1	+25°C	-4	-	mA
			2, 3	+125°C, -55°C	-4	-	mA
Power Supply	+PSRR	$\Delta V_{SUP} = 14V$	1	+25°C	86	-	dB
Rejection Ratio		ΔV_{SUP} = 13.5V	2, 3	+125°C, -55°C	86	-	dB
	-PSRR	$\Delta V_{SUP} = 14V$	1	+25°C	86	-	dB
		ΔV _{SUP} = 13.5V	2, 3	+125°C, -55°C	86	-	dB
Offset Voltage	+V _{IO} Adj	Note 1	1	+25°C	V _{IO} -1	-	mV
Adjustment			2, 3	+125°C, -55°C	V _{IO} -1	-	mV
	-V _{IO} Adj	Note 1	1	+25°C	V _{IO} +1	-	mV
			2, 3	+125°C, -55°C	V _{IO} +1	-	mV

NOTE:

- 1. Offset adjustment range is [V_{IO} (Measured) ±1mV] minimum referred to output. This test is for functionality only to assure adjustment through 0V.
- 2. For differential input voltages greater than 0.7V, the input current must be limited to 25mA to protect the back-to-back input diodes.

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Device Tested at: $V_{SUPPLY} = \pm 15V$, $R_{SOURCE} = 50\Omega$, $R_{LOAD} = 2k\Omega$, $C_{LOAD} = 50pF$, $A_{VCL} = +1V/V$, Unless Otherwise Specified.

			GROUP A		LIMITS		
PARAMETERS	SYMBOL	CONDITIONS	SUBGROUP	TEMPERATURE	MIN	MAX	UNITS
Slew Rate	+SR	$V_{OUT} = -3V \text{ to } +3V$	7	+25°C	7	-	V/μs
	-SR	V _{OUT} = +3V to -3V	7	+25°C	7	-	V/μs
Rise and Fall Time	t _R	V_{OUT} = 0 to +200mV 10% \leq T _R \leq 90%	7	+25°C	-	150	ns
	t _F	V_{OUT} = 0 to -200mV 10% \leq T _F \leq 90%	7	+25°C	-	150	ns
Overshoot	+OS	V _{OUT} = 0 to +200mV	7	+25°C	-	40	%
	-OS	V _{OUT} = 0 to -200mV	7	+25°C	-	40	%

TABLE 3. ELECTRICAL PERFORMANCE CHARACTERISTICS

Device Characterized at: $V_{SUPPLY} = \pm 15V$, $R_{LOAD} = 2k\Omega$, $C_{LOAD} = 50pF$, $A_V = +1V/V$, Unless Otherwise Specified.

					LIMITS		
PARAMETERS	SYMBOL	CONDITIONS	NOTES	TEMPERATURE	MIN	MAX	UNITS
Average Offset Voltage Drift	V _{IO} TC	V _{CM} = 0V	1	-55°C to +125°C	-	1.8	μV/°C
Differential Input Resistance	R _{IN}	V _{CM} = 0V	1	+25°C	0.8	-	МΩ

TABLE 3. ELECTRICAL PERFORMANCE CHARACTERISTICS

Device Characterized at: $V_{SUPPLY} = \pm 15V$, $R_{LOAD} = 2k\Omega$, $C_{LOAD} = 50pF$, $A_V = +1V/V$, Unless Otherwise Specified.

					LIMITS		
PARAMETERS	SYMBOL	CONDITIONS	NOTES	TEMPERATURE	MIN	MAX	UNITS
Low Frequency Peak-to-Peak Noise	E _{NP-P}	0.1Hz to 10Hz	1	+25°C	-	0.25	μV _{P-P}
Input Noise Voltage Density	E _N	$R_S = 20\Omega, f_O = 10Hz$	1	+25°C	-	10.0	nV/√Hz
		$R_S = 20\Omega$, $f_O = 100Hz$	1	+25°C	-	5.6	nV/√Hz
		$R_S = 20\Omega$, $f_O = 1$ kHz	1	+25°C	-	4.5	nV/√Hz
Input Noise Current Density	I _N	$R_S = 2M\Omega$, $f_O = 10Hz$	1	+25°C	-	4.0	pA/√Hz
		$R_S = 2M\Omega$, $f_O = 100Hz$	1	+25°C	-	2.3	pA/√Hz
		$R_S = 2M\Omega$, $f_O = 1kHz$	1	+25°C	-	0.6	pA/√Hz
Unity Gain Bandwidth	UGBW	V _O = 100mV	1	+25°C	5	-	MHz
Full Power Bandwidth	FPBW	V _{PEAK} = 10V	1, 2	+25°C	111	-	kHz
Minimum Closed Loop Stable Gain	CLSG	$R_L = 2k\Omega$, $C_L = 50pF$	1	-55°C to +125°C	±1	-	V/V
Settling Time	t _S	To 0.1% for a 10V Step	1	+25°C	-	2	μS
Output Resistance	R _{OUT}	Open Loop	1	+25°C	-	100	Ω
Quiescent Power Consumption	PC	V _{OUT} = 0V, I _{OUT} = 0mA	1, 3	-55°C to +125°C	-	120	mW

NOTES:

- 1. Parameters list and highly are controlled via design or process parameters are lab characterized upon initial design release, or upon design changes. These parameters are guaranteed by characterization based upon data from multiple production runs which reflect lot to lot and within lot variation.
- 2. Full Power Bandwidth guarantee based on Slew Rate measurement using FPBW = Slew Rate/(2πV_{PEAK}).
- 3. Quiescent Power Consumption based upon Quiescent Supply Current test maximum. (No load on output.)

TABLE 4. ELECTRICAL TEST REQUIREMENTS

MIL-STD-883 TEST REQUIREMENTS	SUBGROUPS (SEE TABLES 1 AND 2) (NOTE 2)
Interim Electrical Parameters (Pre Burn-In)	1
Final Electrical Test Parameters	1 (Note 1), 2, 3, 4, 5, 6, 7
Group A Test Requirements	1, 2, 3, 4, 5, 6, 7
Groups C and D Endpoints	1

NOTES:

- 1. PDA applies to Subgroup 1 only.
- 2. The Subgroup assignments of the parameters in these tables were patterned after Mil-M-38510/135, with the exception of V_{IO}, which is Subgroups 1, 2, 3.

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Die Characteristics

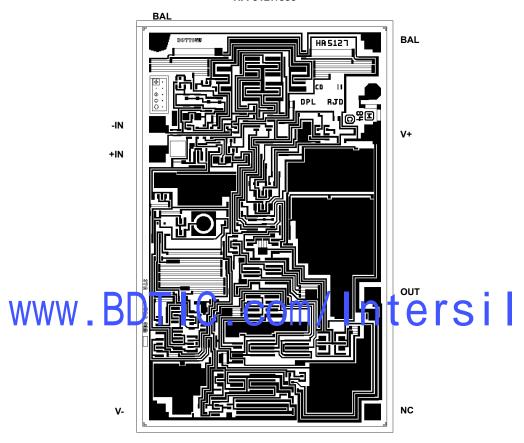
SUBSTRATE POTENTIAL (Powered Up): V-

TRANSISTOR COUNT: 63

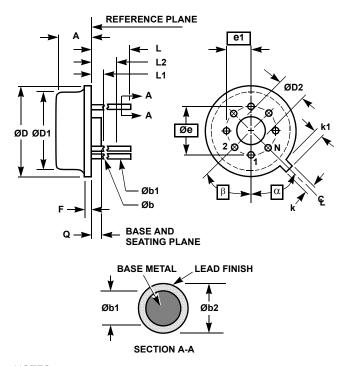
PROCESS: Bipolar Dielectric Isolation

Metallization Mask Layout

HA-5127/883



Metal Can Packages (Can)



NOTES:

- 1. (All leads) Øb applies between L1 and L2. Øb1 applies between L2 and 0.500 from the reference plane. Diameter is uncontrolled in L1 and beyond 0.500 from the reference plane.
- 2. Measured from inaximum diam tor of the product.
- α is the basic spacing from the centerline of the tab to terminal and β is the basic spacing of each lead or lead position (N -1 places) from α, looking at the bottom of the package.
- 4. N is the maximum number of terminal positions.
- 5. Dimensioning and tolerancing per ANSI Y14.5M 1982.

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6. Controlling dimension: INCH.

T8.C MIL-STD-1835 MACY1-X8 (A1) 8 LEAD METAL CAN PACKAGE

	INCHES		MILLIN	IETERS	
SYMBOL	MIN	MAX	MIN	MAX	NOTES
Α	0.165	0.185	4.19	4.70	-
Øb	0.016	0.019	0.41	0.48	1
Øb1	0.016	0.021	0.41	0.53	1
Øb2	0.016	0.024	0.41	0.61	-
ØD	0.335	0.375	8.51	9.40	-
ØD1	0.305	0.335	7.75	8.51	-
ØD2	0.110	0.160	2.79	4.06	-
е	0.200	0.200 BSC 5.08 BSC		BSC	-
e1	0.100	BSC	2.54	BSC	-
F	-	0.040	-	1.02	-
k	0.027	0.034	0.69	0.86	-
k1	0.027	0.045	0.69	1.14	2
L	0.500	0.750	12.70	19.05	1
L1	-	0.050	-	1.27	1
L2	0.250	-	6.35	-	1
Q	0.010	0.045	0.25	1.14	-
α	45°	BSC	45° BSC		3
β	45°	BSC	45°	3	
nh /	n	te	re	8	4
JIII/		ιC		Rev	. 0 5/18/94

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